

Description

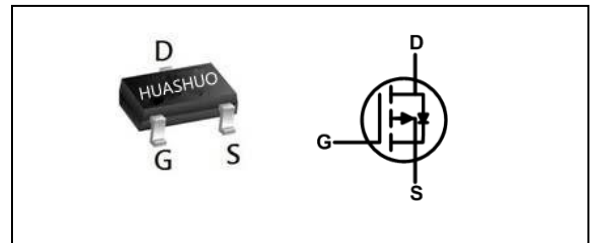
The HSS2607 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications

The HSS2607 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	-20	V
R _{DS(ON),typ}	25	mΩ
I _D	-5	A

SOT23 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ -4.5V ₁	-5	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ -4.5V ₁	-3.8	A
I _{DM}	Pulsed Drain Current ₂	-18.8	A
P _D @T _A =25°C	Total Power Dissipation ₃	1	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ₁	---	125	°C/W
R _{θJC}	Thermal Resistance Junction-Case ₁	---	80	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B _{VDS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔB _{VDS} /ΔT _J	B _{VDS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.01	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ₂	V _{GS} =-4.5V, I _D =-4A	---	25	32	mΩ
		V _{GS} =-2.5V, I _D =-2A	---	32	40	
		V _{GS} =-1.8V, I _D =-1.5A	---	42	55	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.3	-0.5	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2.96	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-16V, V _{GS} =0V, T _J =55°C	---	---	-5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-4A	---	21	---	S
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-4A	---	27.3	38.2	nC
Q _{gs}	Gate-Source Charge		---	3.6	5.0	
Q _{gd}	Gate-Drain Charge		---	6.5	9.1	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3Ω I _D =-4A	---	9.2	18.4	ns
T _r	Rise Time		---	59	106	
T _{d(off)}	Turn-Off Delay Time		---	99	198	
T _f	Fall Time		---	71	142	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	2280	3192	pF
C _{oss}	Output Capacitance		---	220	308	
C _{rss}	Reverse Transfer Capacitance		---	187	262	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current _{1,4}	V _G =V _D =0V, Force Current	---	---	-4.7	A
I _{SM}	Pulsed Source Current _{2,4}		---	---	-18.8	A
V _{SD}	Diode Forward Voltage ₂	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
t _{rr}	Reverse Recovery Time	I _F =-4A, di/dt=100A/μs, T _J =25°C	---	52	---	nS
Q _{rr}	Reverse Recovery Charge		---	28	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

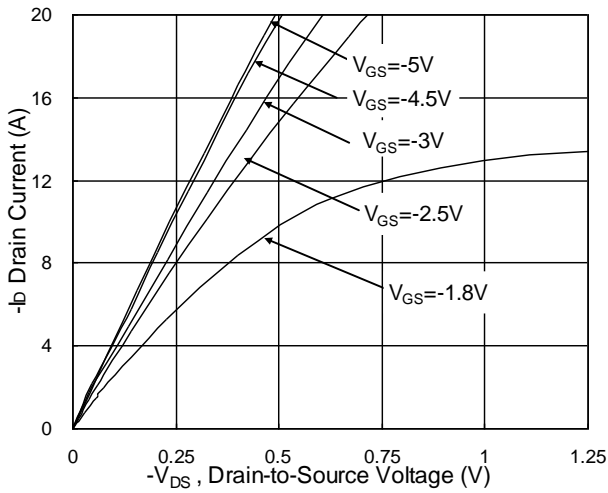


Fig.1 Typical Output Characteristics

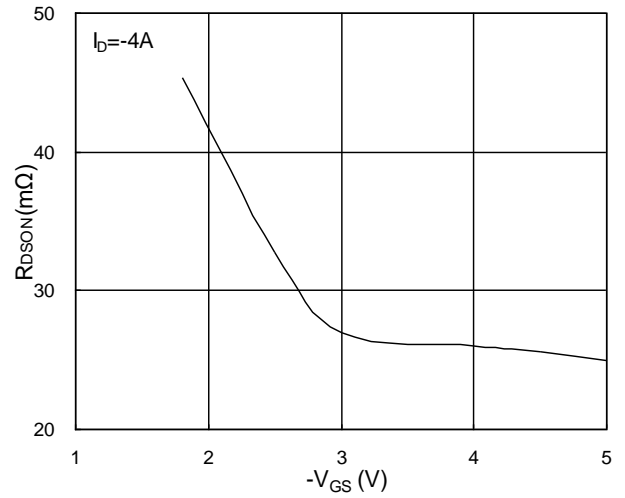


Fig.2 On-Resistance vs. Gate-Source

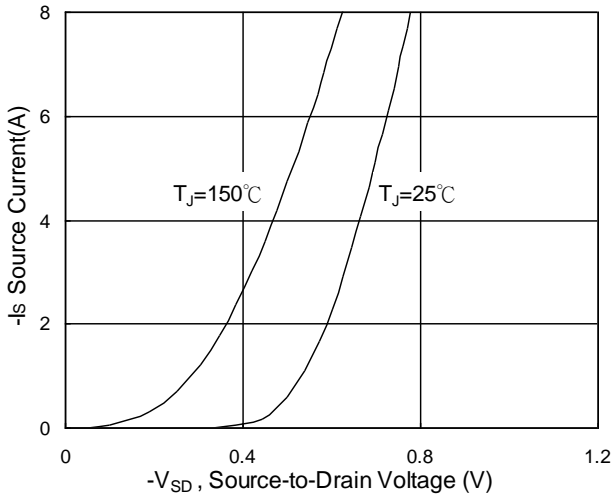


Fig.3 Forward Characteristics Of Reverse

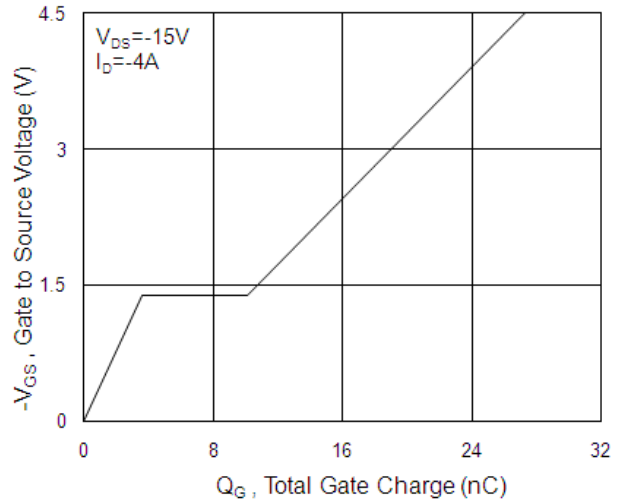


Fig.4 Gate-Charge Characteristics

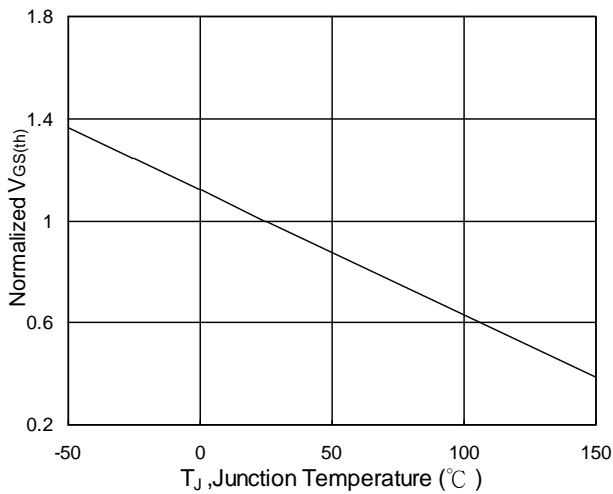


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

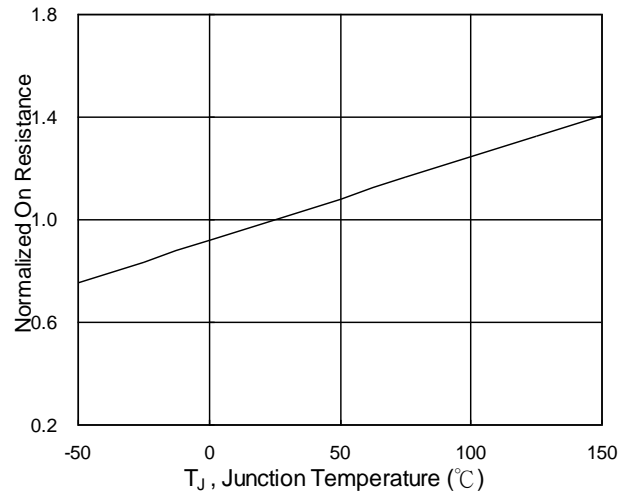


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

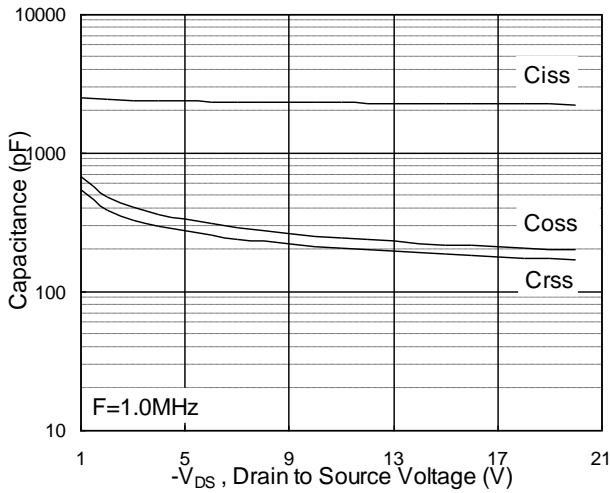


Fig.7 Capacitance

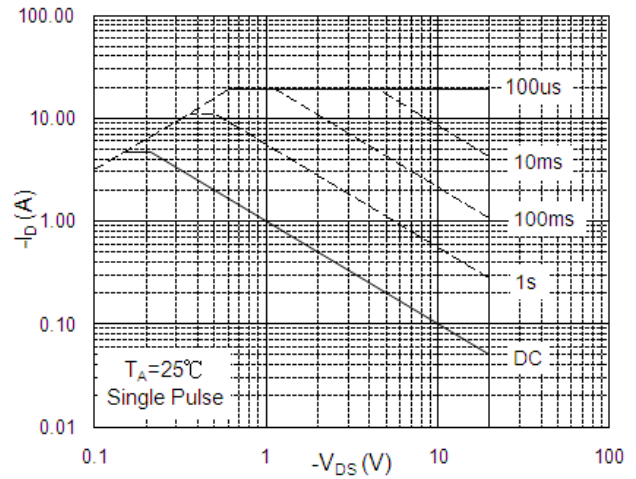


Fig.8 Safe Operating Area

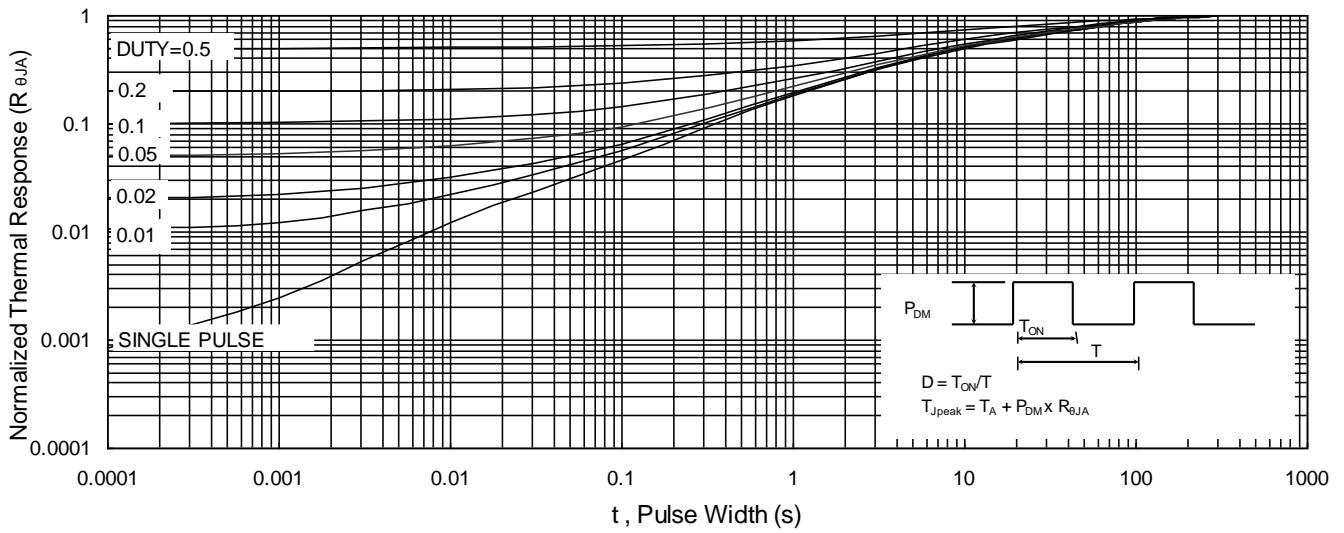


Fig.9 Normalized Maximum Transient Thermal Impedance

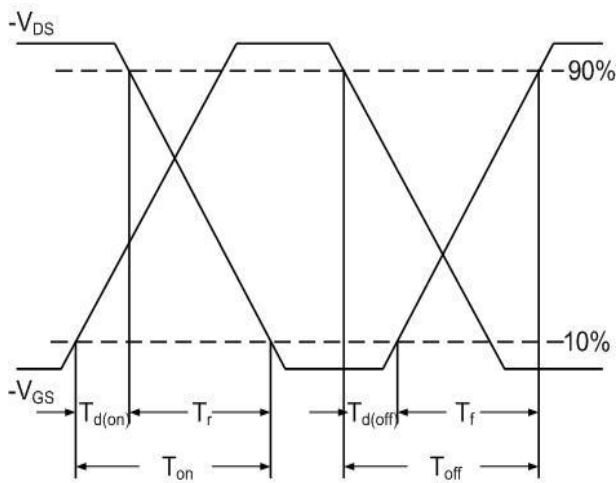


Fig.10 Switching Time Waveform

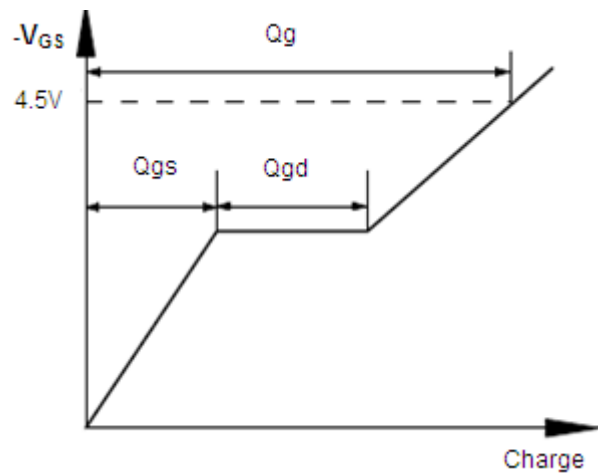
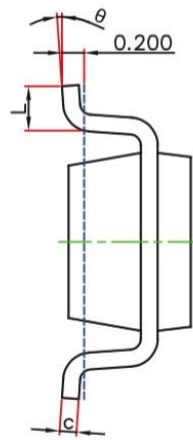
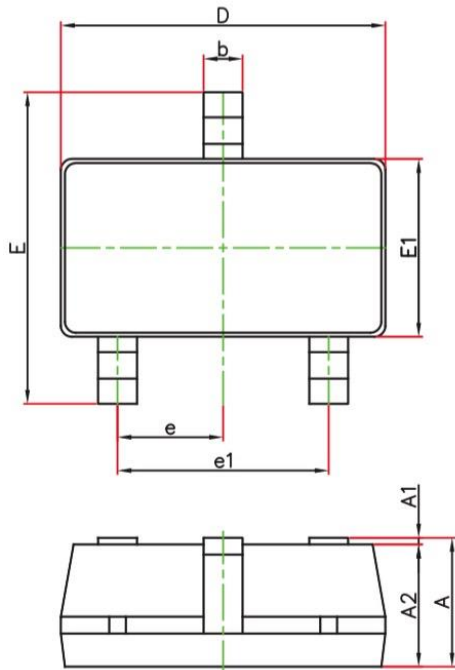


Fig.11 Gate Charge Waveform



Ordering Information

Part Number	Package code	Packaging
HSS2607	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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